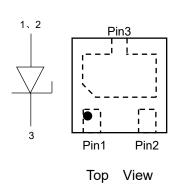




## **Transient Voltage Suppressor**

#### **Description**

The PTVSHC3N24VU ESD protector is designed to replace multilayer varistors (MLVs) in portable applications such as cell phones, notebook computers, and PDA's. They feature large cross-sectional area junctions for conducting high transient currents, offer desirable electrical characteristics for board level protection, such as fast response time, lower operating voltage, lower clamping voltage and no device degradation when compared to MLVs. The PTVSHC3N24VU protects sensitive semiconductor components from damage or upset due to electrostatic discharge (ESD) and other voltage induced transient events. The PTVSHC3N24VU is available in a DFN2×2-3L package with working voltages of 24 volt. It is used to meet the ESD immunity requirements of IEC 61000-4-2 (±30kV air, ±30kV contact discharge)



#### **Feature**

- 6000W Peak pulse power per line (t<sub>P</sub> = 8/20µs)
- DFN2×2-3L package
- Response time is typically < 1 ns</p>
- Protect one I/O or power line
- RoHS compliant
- Transient protection for data lines to IEC 61000-4-2(ESD) ±30KV(air), ±30KV(contact); IEC 61000-4-4 (EFT) 80A (5/50ns), IEC 61000-4-5 (Lightning) 110A (8/20us)

### **Applications**

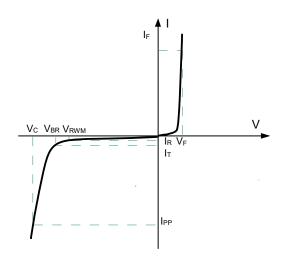
- Cell phone handsets and accessories
- Personal digital assistants (PDA's)
- Notebooks, desktops, and servers
- Portable instrumentation
- Cordless phones
- Digital cameras
- Peripherals
- MP3 players

#### **Mechanical Characteristics**

- Lead finish:100% matte Sn(Tin)
- Mounting position: Any
- Qualified max reflow temperature:260°C
- Pure tin plating: 7 ~ 17 um

# **Electronics Parameter**

Symbol	Parameter	
V <sub>RWM</sub>	Peak Reverse Working Voltage	
I <sub>R</sub>	Reverse Leakage Current @ V <sub>RWM</sub>	
V <sub>BR</sub>	Breakdown Voltage @ I⊤	
I <sub>T</sub>	Test Current	
I <sub>PP</sub>	Maximum Reverse Peak Pulse Current	
Vc	Clamping Voltage @ IPP	
P <sub>PP</sub>	Peak Pulse Power	
CJ	Junction Capacitance	
lF	Forward Current	
VF	Forward Voltage @ I <sub>F</sub>	



## Electrical characteristics per line@25℃( unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Peak Reverse Working Voltage	V <sub>RWM</sub>				24	V
Breakdown Voltage	V <sub>BR</sub>	I <sub>t</sub> =1mA	25	27	30	V
Reverse Leakage Current	I <sub>R</sub>	V <sub>RWM</sub> =24V			1	μΑ
Maximum Reverse Peak Pulse Current	IPP			110		Α
Clamping Voltage	Vc	I <sub>PP</sub> =70A t <sub>P</sub> = 8/20μs		45	48	V
Clamping Voltage	Vc	I <sub>PP</sub> =100A t <sub>P</sub> = 8/20µs		51	54	V
Junction Capacitance	Cj	V <sub>R</sub> =0V f = 1MHz		635	680	pF

Notes: Measured from pin 3 to pin 1 and pin 2.

## **Absolute maximum rating@25℃**

Rating	Symbol	Value	Units
Peak Pulse Power(t₂ = 8/20μS)	P <sub>pp</sub>	6000	W
Lead Soldering Temperature	T∟	260 (10 sec)	℃
Operating Temperature	TJ	-55 to +150	℃
Storage Temperature	T <sub>STG</sub>	-55 to +150	℃

Rev.06.4 2 www.prisemi.com

## **Typical Characteristics**

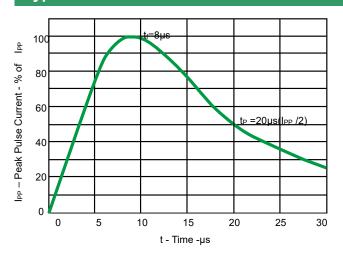


Fig 1.Pulse Waveform

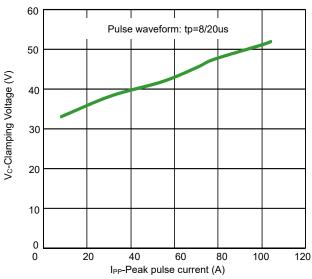


Fig 3. Clamping voltage vs. Peak pulse current

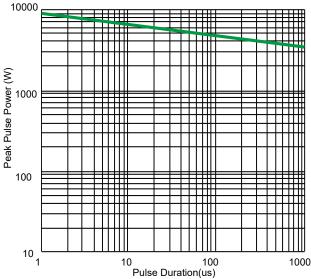


Fig 5. Non Repetitive Peak Pulse Power vs. Pulse time

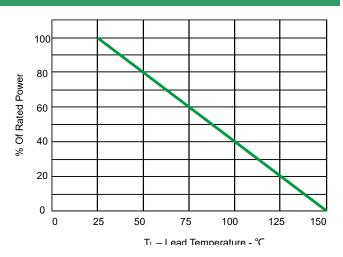


Fig 2.Power Derating Curve

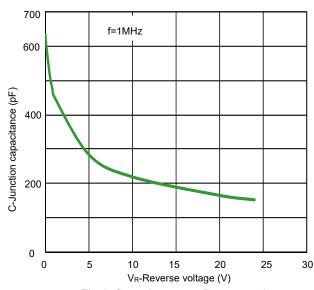


Fig 4. Capacitance vs. Reveres voltage

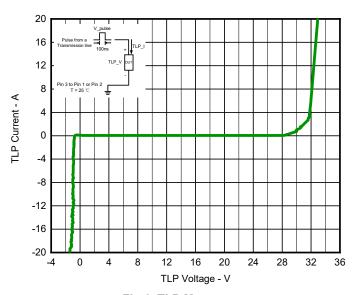
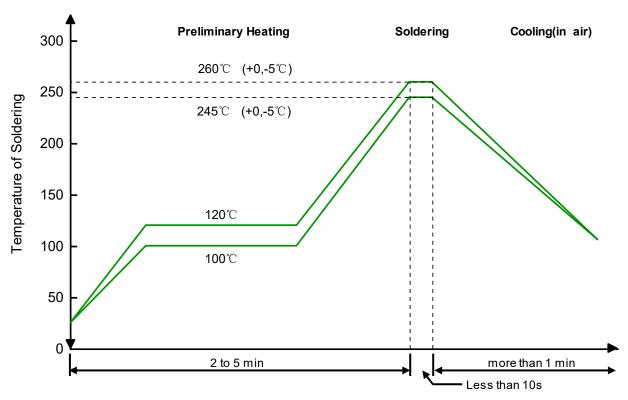


Fig 6. TLP Measurement

#### **Solder Reflow Recommendation**



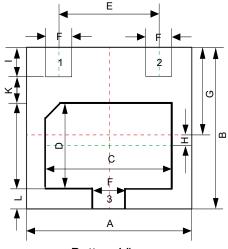
Remark: Pb free for 260°C; Pb for 245°C.

### **PCB Design**

For TVS diodes a low-ohmic and low-inductive path to chassis earth is absolutely mandatory in order to achieve good ESD protection. Novices in the area of ESD protection should take following suggestions to heart:

- Do not use stubs, but place the cathode of the TVS diode directly on the signal trace.
- Do not make false economies and save copper for the ground connection.
- Place via holes to ground as close as possible to the anode of the TVS diode.
- > Use as many via holes as possible for the ground connection.
- Keep the length of via holes in mind! The longer the more inductance they will have.

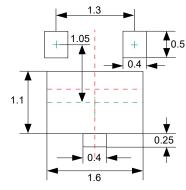
# Product dimension (DFN2×2-3L)





**Bottom View** 

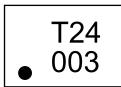
Dim	Millimeters		
Dim	MIN	MAX	
Α	1.90	2.10	
В	1.90	2.10	
С	1.40	1.60	
D	0.90	1.10	
E	1.30BSC		
F	0.25	0.35	
G	0.95	1.05	
Н	0.20	0.30	
I	0.35	0.45	
J		0.65	
K	0.30 0.35		
L	0.15	0.20	



Unit:mm

Recommended Soldering Pad

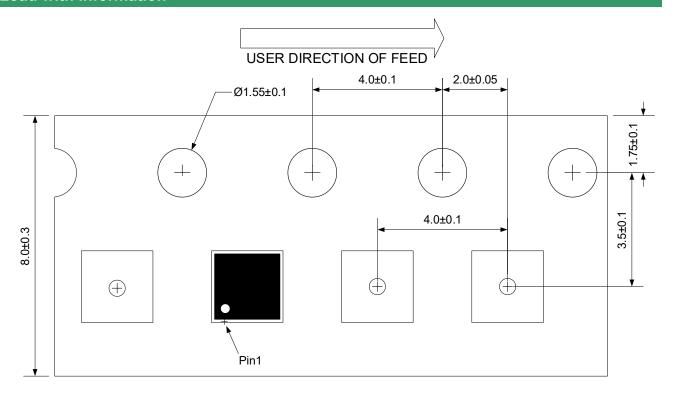
## Marking information



## Ordering information

Device	Package	Reel	Shipping
PTVSHC3N24VU	DFN2×2-3L (Pb-Free)	7"	3000 / Tape & Reel

## **Load with information**



Unit:mm

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